Foldable Technology of OLED Displays
Chair: Koichi Miwa (LG Display Co., Ltd)
Co-Chair: Keisuke Omoto (Apple)
Wed. Nov 27, 2019 1:40 PM - 3:15 PM Mid-sized Hall B (1F)

Positive Bias-Stress Stability of Flexible Amorphous InGaZnO Thin Film Transistors with Double-Stacked Gate Insulators
*Chengyuan Dong¹, Guochao Liu¹, Ying Zhang¹, Guofeng Feng¹, Wen Zhang¹ (1. Shanghai Jiao Tong University (China))
Keywords:flexible, a-IGZO TFT, Double-stacked Gate Insulator, PBS

Double-stacked gate insulators (SiOₓ/TaOₓ) made flexible amorphous InGaZnO thin film transistors more stable under both mechanical bending and positive bias-stress, which was assumed to result from their better neutral plane position and front-channel interface states. A simple model was built to explain this improvement effect.